

# Radiation Physics

## A. Basics of Radiation

### A.1. Cross section

→ The number of interactions detected can be calculated as:

$$N_{\text{detector}} = I \cdot n \cdot x \cdot \epsilon \cdot \sigma_{\text{total}} \quad (1)$$

where:

- $I = \frac{dN_{\text{incident}}}{dt}$  is the incident particle flux (rate of incident particles),
- $n = \frac{dN_{\text{scatterer}}}{dV} = \frac{N_{AV}}{A} \rho$  is the number density of scatterers, with:

$$\rho = \text{Material density}, \quad N_{AV} = \text{Avogadro's number},$$

$$A = \text{atomic weight of the material.}$$

- $\epsilon = \epsilon_{\text{intrinsic}} \cdot \epsilon_{\text{geo}}$  is the detection efficiency, consisting of:

$$\epsilon_{\text{geo}} = \frac{S}{d^2},$$

where  $S$  is the sensitive area of the detector and  $d$  is the distance between the detector and the interaction point. -  $\sigma_{\text{total}}$  is the total cross section, which can be expressed as an integral over the solid angle:

$$\sigma_{\text{total}} = \int \frac{d\sigma(\theta, E)}{d\Omega} d\Omega,$$

where  $\frac{d\sigma(\theta, E)}{d\Omega}$  represents the differential cross section as a function of angle  $\theta$  and energy  $E$ .

→ Assume an interaction:  $A(a, b)B$

- $I_a$  = current of incident particles  $a$ ; number of particles per unit time
- $N_T$  = number of target nuclei per unit area
- $R_b$  = number of detected particles  $b$  per unit time (reaction rate)

$$R_b \propto I_a N_T$$

Define the **cross section**  $\sigma$ :

$$\sigma = \frac{R_b}{I_a N_T}$$

The cross section  $\sigma$  has the dimension of **area**. The standard unit for cross section is the **barn**:

$$1 \text{ barn} = 10^{-24} \text{ cm}^2 = 100 \text{ fm}^2$$

$$\rightarrow I = I_0 e^{-\sigma n x} = I_0 e^{-\mu x}, \quad (2)$$

where  $I_0$  is the initial intensity of the incident radiation,  $x$  is the thickness of the material, and  $\mu$  is the linear attenuation coefficient, defined as  $\mu = \sigma n$ .

→ For a mixture or compound, the mass attenuation coefficient  $\left(\frac{\mu}{\rho}\right)$  can be expressed as:

$$\left(\frac{\mu}{\rho}\right) = \sum w_i \left(\frac{\mu}{\rho}\right)_i, \quad (3)$$

### A.2. Lab coordinate and Center-Of-Mass coordinate

→ **Angle Transformation:**

$$\tan(\theta_{\text{lab}}) = \frac{\sin(\theta_{\text{cm}})}{\gamma + \cos(\theta_{\text{cm}})}$$

→ **Solid Angle Transformation:**

$$d\Omega_{\text{lab}} = \frac{|1 + \gamma \cos(\theta_{\text{cm}})|}{(1 + \gamma^2 + 2\gamma \cos(\theta_{\text{cm}}))^{3/2}} d\Omega_{\text{cm}}$$

→ **Energy Transformation:**

$$E_{\text{cm}} = \frac{M_a}{M_a + M_A} E_{\text{lab}}$$

→ **Definition of  $\gamma$ :**

$$\gamma = \sqrt{\frac{M_a M_b}{M_A M_B} \cdot \frac{E_{\text{cm}}}{E_{\text{cm}} + Q}} \approx \frac{M_a}{M_A}$$

## B. Interaction of Photon and matter

### B.1. Photoelectric effect

→ **Moseley's Law:**

$$E_n = R h c \frac{(Z - s_n)^2}{n^2}$$

where:

- $R$  is the Rydberg constant,
- $Z$  is the atomic number of the element,
- $s_n$  is the screening constant that accounts for the shielding effect of inner electrons,

→ **Cross-Section Dependence:**

$$\sigma_{\text{TK}} = \alpha^4 (e \sigma_{\text{Th}}) Z^n \sqrt{\frac{32 m_e c^2}{E^2}},$$

$$n \approx 4 (\text{low energies}), \quad n \approx 4.6 - 4.8 (\text{high energies}).$$

### B.2. Scattering

→ **Rayleigh Scattering**

- Type: Elastic scattering, Coherent
- Interaction Mechanism: Interaction of photons with bound electrons in an atom without energy transfer. It occurs when the incident photon's wavelength is much larger than the size of the particle.
- Differential Cross Section:

$$\frac{d\sigma}{d\Omega} \propto r_0^2 \left( \frac{1 + \cos^2 \theta}{2} \right) \cdot \left[ F \left( \frac{\sin(\theta/2)}{\lambda}, Z \right) \right]^2 \cdot 2\pi \sin \theta$$

where  $F \left( \frac{\sin(\theta/2)}{\lambda}, Z \right)$  is the atomic form factor that depends on the scattering angle and atomic number  $Z$ . This factor accounts for the constructive interference of scattered waves, leading to coherent scattering.

→ **Thomson Scattering**

- Type: Elastic scattering, Coherent
- Interaction Mechanism: Scattering of low-energy photons by free or loosely bound electrons. It occurs in the limit of low photon energy, where the electron remains non-relativistic.
- Differential Cross Section:

$$\frac{d\sigma}{d\Omega} = r_0^2 \left( \frac{1 + \cos^2 \theta}{2} \right)$$

This describes the scattering of electromagnetic waves off free electrons, assuming no change in photon energy.

→ **Compton Scattering**

- Type: Inelastic scattering, Incoherent
- Interaction Mechanism: Photon-electron interaction causing an energy transfer from the photon to the electron, resulting in a lower-energy scattered photon and a recoiling electron. It is significant at higher photon energies where energy transfer cannot be ignored.
- Differential Cross Section: The differential cross-section for Compton scattering is given by the Klein-Nishina formula:

$$\frac{d\sigma}{d\Omega} = r_0^2 \cdot \frac{1 + \cos^2 \theta}{2} \cdot \left[ \frac{1}{1 + \alpha(1 - \cos \theta)} \right]^2 \cdot \left[ 1 + \frac{\alpha^2(1 - \cos \theta)^2}{(1 + \cos^2 \theta)(1 + \alpha(1 - \cos \theta))} \right]$$

where  $\alpha = \frac{E_\gamma}{m_e c^2}$  is the normalized photon energy. This formula reflects the dependence of the cross-section on the scattering angle  $\theta$  and the photon's initial energy  $E_\gamma$ . The energy of the scattered photon  $E'_\gamma$  is given by:

$$E'_\gamma = \frac{E_\gamma}{1 + \frac{E_\gamma}{m_e c^2} (1 - \cos \theta)}$$

The Compton shift, which represents the wavelength change due to scattering, is expressed as:

$$\Delta \lambda = \lambda' - \lambda = \frac{h}{m_0 c} (1 - \cos \theta)$$

### B.3. Pair/Triple production

→ **Threshold Energy:**

- For **Pair Production**, the photon energy must exceed the combined rest mass energy of an electron-positron pair:

$$h\nu_{\text{threshold}} = 2m_e c^2 \approx 1.022 \text{ MeV}$$

- For **Triple Production**, involving an additional electron, the threshold energy is:

$$h\nu_{\text{threshold}} = 4m_e c^2 \approx 2.044 \text{ MeV}$$

→ **Cross-Section Approximation:** The cross-section  $\sigma$  for pair and triple production processes is approximately proportional to the square of the atomic number  $Z$  and the logarithm of the incident photon energy  $E_\gamma$ :

$$\sigma \approx Z^2 \ln(E_\gamma + C)$$

where  $C$  is a constant that depends on the material properties and interaction parameters. This logarithmic dependence indicates that the cross-section increases with increasing photon energy but at a decreasing rate.

### B.4. Photon-Nuclear Interaction

→ **Description:** Photon-nuclear interactions occur when high-energy photons (typically above a few MeV) interact with a nucleus, causing nuclear reactions. These interactions can result in the emission of particles such as neutrons, protons, or even alpha particles. The most common photon-nuclear processes include the *photo-neutron* and *photo-proton* reactions.

→ **Photonuclear Reactions:** The general form of photonuclear reactions can be represented as:

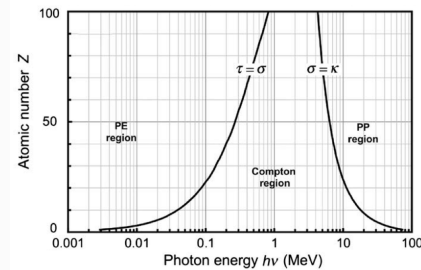
$$\gamma + {}^A_Z X \rightarrow {}^{A-1}_{Z-1} X + n$$

or

$$\gamma + {}^A_Z X \rightarrow {}^{A-1}_{Z-1} Y + p$$

where:

- $\gamma$  represents the incident high-energy photon,
- ${}_Z^A X$  is the target nucleus with atomic number  $Z$  and mass number  $A$ ,
- $n$  denotes the emitted neutron, and  $p$  denotes the emitted proton,
- ${}^{A-1}_{Z-1} X$  and  ${}^{A-1}_{Z-1} Y$  are the resulting daughter nuclei.



## C. Interaction of charged particle and matter

### C.1. Stopping Power and Collision Types

→ **Stopping Power:**

- **Collision Stopping Power:** This represents the energy loss due to inelastic collisions with atomic electrons. These collisions lead to ionization and excitation of atoms within the material.
- **Radiation Stopping Power:** This accounts for energy loss due to the emission of bremsstrahlung radiation, which occurs when a charged particle is decelerated by the electric field of a nucleus.

$$S = \frac{dE}{dx} = S_{\text{rad}} + S_{\text{col}}$$

→ **Collision Types:**

- **Close/Hard Collisions:**  $b \approx a$
- **Far/Soft Collisions:**  $b \gg a$
- **Radiation/Bremsstrahlung Collisions:**  $b \ll a$

### C.2. Stopping Power Concepts

→ **Bohr Classical Formula:** A model describing the energy loss of charged particles due to Coulomb interactions with atomic electrons. The formula gives an approximation for the stopping power at lower energies.

$$S_{\text{col}} = 4\pi \frac{Z N_A}{A} \left( \frac{e^2}{4\pi\epsilon_0} \right)^2 \frac{z^2}{m_e v^2} \ln \frac{b_{\text{max}}}{b_{\text{min}}}$$

$$S_{\text{col}} = 2\pi \frac{Z N_A}{A} \left( \frac{e^2}{4\pi\epsilon_0} \right)^2 \frac{z^2}{m_e v^2} \ln \frac{2mv^2}{I}$$

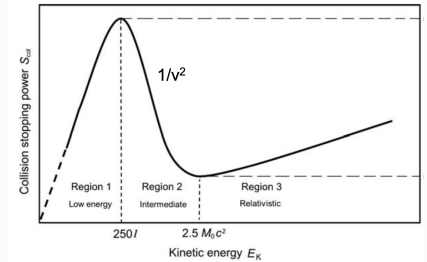
→ **Bethe Equation:** The Bethe formula describes the stopping power of charged particles moving through matter. It is given by:

$$S_{\text{col}} = S^{\text{hard}} + S^{\text{soft}} = 4\pi \frac{Z N_A}{A} \left( \frac{e^2}{4\pi\epsilon_0} \right)^2 \frac{z^2}{m_e c^2 \beta^2} \left\{ \ln \frac{2m_e c^2}{1 - \beta^2} + \ln \frac{\beta^2}{1 - \beta^2} - \beta^2 \right\}$$

where  $I$  is the mean excitation potential.

→ **Fano Correction:** A correction term applied to the Bethe equation to account for deviations from the classical assumptions in the stopping power calculation, particularly for electrons and positrons.

$$4\pi \frac{N_A}{A} \left( \frac{e^2}{4\pi\epsilon_0} \right)^2 \frac{z^2 Z}{m_e c^2 \beta^2} \left\{ \ln \frac{2m_e c^2}{I} + \ln \frac{\beta^2}{1 - \beta^2} - \beta^2 - \frac{C}{Z} - \delta \right\}$$



→ **Mass Stopping Power:** The stopping power normalized by the density of the absorbing material, for compounds:

$$\frac{1}{\rho} \frac{dE}{dx} = \sum_i w_i \frac{1}{\rho_i} \left( \frac{dE}{dx} \right)_i$$

$$w_i = (\alpha_i A_i) / \sum \alpha_i A_i$$

→ **CSDA Range:** The Continuous Slowing Down Approximation (CSDA) range is the total distance a charged particle travels in a material as it loses energy continuously. It is calculated by integrating the reciprocal of the stopping power:

$$R_{\text{CSDA}} = \int_0^{(E_K)_0} \frac{dE}{S_{\text{tot}}(E)} = \int_{E_0}^0 \frac{dx}{dE} dE = \int_{E_0}^0 \frac{1}{(dE/dx)} dE [\text{cm}]$$

or

$$R_{m\_CSDA} = \int_{E_0}^0 \frac{d\xi}{dE} dE = \int_{E_0}^0 \frac{1}{(dE/d\xi)} dE \quad [\text{g/cm}^2]$$

→ **Substitution Rule:** For two different materials with charges  $Z_1, Z_2$ , and masses  $m_1, m_2$ , the range can be related as:

$$\left( \frac{dE}{d\xi} \right) |_{(E_2)} = \frac{Z_2^2}{Z_1^2} \left( \frac{dE}{d\xi} \right) |_{(E_1)}$$

$$R_2(E_2) = \frac{m_2 Z_1^2}{m_1 Z_2^2} R_1(E_1), \quad \text{where} \quad E_1 = E_2 \frac{m_1}{m_2}$$

→ **Bragg-Kleeman Rule:**

$$\frac{(R_1/\rho_1)}{(R_2/\rho_2)} = \frac{\sqrt{A_1}}{\sqrt{A_2}}$$

→ **Critical Energy ( $E_c$ ):** The critical energy is the energy at which the energy loss due to radiation (bremsstrahlung) becomes equal to the energy loss due to collisions. It is given by:

$$\frac{(dE/dx)_{\text{rad}}}{(dE/dx)_{\text{col}}} \approx \frac{E_k Z}{800} \cdot (E_k)_{\text{critical}} = \frac{800}{Z}$$

→ **Radiation Yield ( $Y$ ):** The fraction of the total energy loss due to radiation as opposed to collisions. For electrons, the yield is approximated by:

$$Y = \frac{E_{\text{rad}}}{E_{\text{total}}} \approx \frac{6 \times 10^{-4} ZT}{1 + 6 \times 10^{-4} ZT}$$

where  $Z$  is the atomic number of the material and  $T$  is the kinetic energy of the particle.

## D. Neutron physics

### D.1. Energy Classifications of Neutrons

Neutrons can be classified based on their energy levels into several categories:

- **Slow (Cold) Neutrons:** Energy Range: 0 – 0.005 eV
- **Thermal Neutrons:** Energy Range: 0.005 – 0.5 eV
- **Epithermal Neutrons:** Energy Range: 0.5 – 1000 eV
- **Intermediate Neutrons:** Energy Range: 1 – 100 keV
- **Fast Neutrons:** Energy Range: 0.1 – 10 MeV

Neutrons also interact differently with target nuclei based on their mass number  $A$ :

- **Light Nuclei:** Mass Number:  $A < 25$
- **Medium Nuclei:** Mass Number:  $25 < A < 80$
- **Heavy Nuclei:** Mass Number:  $A > 80$

### D.2. Neutron Sources

Neutrons can be sourced from various processes, including:

- **Fission:** Neutrons are produced during the fission of heavy nuclei.
- **Particle Accelerators:** High-energy particle collisions can produce neutrons.
- **( $\alpha, n$ ) Reactions:** Neutrons are emitted when alpha particles interact with certain materials.
- **( $\gamma, n$ ) Reactions:** Neutrons are produced when gamma rays interact with certain nuclei.

### D.3. Neutron Reactions

Neutrons can undergo various reactions, primarily classified into scattering and absorption:

- **Scattering:**
  - **Elastic Scattering ( $n, n$ ):**

$$\Delta E_{K\text{max}} = (E_K)_i \frac{4m_n M}{(m_n + M)^2}$$

Kinetic energy of the scattered neutron

$$(E_K)_f = (E_K)_i - \Delta E_{K\text{max}} = (E_K)_i \left( \frac{M - m_n}{M + m_n} \right)^2$$

For certain angle :  $\Delta E_K = (E_K)_i \frac{4m_n M}{(m_n + M)^2} \cos^2 \theta$ . The average energy transfer is given by:

$$\langle \Delta E \rangle = \frac{\Delta E_{K\text{max}}}{2}$$

The average kinetic energy attained by the scattered neutron is

$$(E_K)_f = (E_K)_i - \langle \Delta E \rangle = (E_K)_i \frac{m_n^2 + M^2}{(m_n + M)^2}$$

- **Inelastic Scattering ( $n, n' \gamma$ ):** In this reaction, a neutron is scattered and energy is transferred to the nucleus, resulting in gamma radiation.

→ **Absorption:**

- **Fission:** Absorption of a neutron can lead to the fission of heavy nuclei.
- **Radiative Capture ( $n, \gamma$ ):** A neutron is captured by a nucleus, emitting gamma radiation.
- Other reactions include: ( $n, p$ ); ( $n, d$ ); ( $n, \alpha$ ); ( $n, np$ ); ( $n, 2n$ ); ( $n, 3n$ ); ( $n, f$ )
- Compound nucleus formation  $a + A \rightarrow C^* \rightarrow B + b$

$$mC^2 + Mc^2 + T = M_{CN}c^2 + E_{k=4}$$

- Partial decay lifetimes of compound nucleus states

$$\Gamma = \Gamma_{n,n} + \Gamma_{n,n'\gamma} + \Gamma_{n,\gamma} + \Gamma_{n,p} + \dots$$

Relative probability of radiative capture is therefore  $\frac{\Gamma_{n,\gamma}}{\Gamma}$

- For light nuclei,  $\Gamma_{n,n} \gg \Gamma_{n,\gamma}$

- For heavy nuclei,  $\Gamma_{n,\gamma} \gg \Gamma_{n,n}$

Neutron width increases with energy of resonance:  $\Gamma_{n,n} = \Gamma_{n,0} \sqrt{E}$

- The formula for the Breit-Wigner cross section

$$\sigma_{CN} = \pi \lambda^2 (2l + 1) \frac{\Gamma_a \Gamma}{(E - E_R)^2 + \left( \frac{\Gamma}{2} \right)^2}$$

The decay in to entity b is expressed:

$$\sigma_{ab} = \sigma_{CN} \frac{\Gamma_b}{\Gamma}$$

The energy-dependent cross-sections for compound elastic scattering is given by:

$$\sigma_{n,n} = \pi \lambda^2 \frac{\Gamma_{n,n}^2}{(E - E_R)^2 + \left( \frac{\Gamma}{2} \right)^2}$$

Cross sections for radiative capture:

$$\sigma_{n,\gamma} = \pi \lambda^2 \frac{\Gamma_{n,n} \Gamma_{n,\gamma}}{(E - E_R)^2 + \left( \frac{\Gamma}{2} \right)^2}$$

- When  $E = E_R$ ,  $\sigma_{max} = 4\pi \lambda^2 \frac{\Gamma_{n,n} \Gamma_{n,\gamma}}{\Gamma^2}$ ,

When  $E = E_R \pm \frac{\Gamma}{2}$ ,  $\sigma = \frac{1}{2} \sigma_{max}$

When  $E \rightarrow 0$ ,  $\Gamma \ll E_R$ ,  $\sigma_{n,\gamma} = \pi \lambda_R^2 \frac{\Gamma_{n,n} \Gamma_{n,\gamma}}{E_R^2} \frac{1}{\sqrt{E}} \propto \frac{1}{\sqrt{E}}$

## E. X-ray production

Energy Range	X-ray Type	Typical Application
0.1 - 20 kV	Soft X-rays	Microscopy, surface analysis
20 - 150 kV	Diagnostic X-rays	Medical imaging, diagnostic
150 - 300 kV	Orthovoltage X-rays	Superficial cancer treatment
300 kV – 1 MV	Intermediate Energy X-rays	Therapeutic, deeper tissue treatment
> 1 MV	Megavoltage X-rays	High-energy cancer treatment

→ Bremsstrahlung Radiation Power

$$P = \frac{\mu_0 q^2 a^2}{6\pi c}$$

→ Cross-section of Bremsstrahlung

$$\frac{d\sigma}{dE} \propto \frac{Z^2}{m^2} \frac{\ln^2 E}{E}$$

→ Kramer's law

$$I(E_\gamma) = KZ(T_e - E_\gamma)$$

→ Efficiency Estimation

$$\frac{S_{\text{rad}}}{S_{\text{col}}} \approx \frac{E_k Z}{820} \quad (E_k \text{ in MeV})$$

$$P_{\text{deposited}} = IV, P_{\text{radiated}} = 0.9 \times 10^{-9} ZV^2 I$$

$$\varepsilon = 0.9 \times 10^{-9} ZV$$

## F. Nuclear radiation and radioactive decay

### F.1. Nuclear Binding Energy and Q-value

→ **Nuclear Binding Energy:**

$$\frac{B}{A} = -[M(A, Z) - (A - Z)m_n - Z(m_p + m_e)]$$

$$= -(-a_1 A + a_2 A^{\frac{2}{3}} + a_3 \frac{\left( \frac{A}{2} - Z \right)^2}{A} + a_4 \frac{Z^2}{A^{\frac{3}{3}}} + a_5 \frac{\delta}{A^{3/4}}) / A$$

$$M(A, Z) = (A - Z)m_n + Z(m_p + m_e) - B$$

→ **Q-value:**

$$Q = \sum_{i, \text{before}} M_i c^2 - \sum_{i, \text{after}} M_i c^2 = \sum_{i, \text{after}} B_i - \sum_{i, \text{before}} B_i$$

$$= \sum_{i, \text{before}} \Delta_i - \sum_{i, \text{after}} \Delta_i$$

where  $\Delta[\text{MeV}] = M(A, Z)c^2 - Am_{\text{amu}}c^2$ .

- If  $Q > 0$ , it indicates an exothermic reaction (energy release).

- If  $Q < 0$ , it indicates an endothermic reaction (energy absorption).

### F.2. Decay Type

→ **Alpha Decay ( $\alpha$  decay):**

$$P \rightarrow D + \text{He}, \quad Q = \Delta_P - \Delta_D - \Delta_{\text{He}}$$

→ **Beta Decay ( $\beta$  decay):**

→→ For  $\beta^-$  decay:

$$P \rightarrow D + e^- + \bar{\nu}, \quad Q = \Delta_P - \Delta_D$$

→→ For  $\beta^+$  decay:

$$P \rightarrow D + e^+ + \nu, \quad Q = \Delta_P - \Delta_D - 2m_e c^2$$

→→ For electron capture:

$$P + e^- \rightarrow D + \nu, \quad Q = \Delta_P - \Delta_D - BE(e^-)$$

→ **Gamma Decay ( $\gamma$  decay):**

$$X^m \rightarrow X + \gamma$$

### F.3. Radioactivity

→ **Activity:**

$$A = \lambda N$$

→ **Exponential Decay:**

$$N(t) = N_0 e^{-\lambda t}$$

→ **Mean Life**

$$\tau = \frac{1}{\lambda} = \frac{T}{\ln 2}$$

→ **Special Activity**

$$SA = \frac{6.02 \times 10^{23} \lambda}{M} = \frac{4.17 \times 10^{23}}{MT}$$

### F.4. Serial Radioactive Decay

→ **Decay Chain:** A radioactive nuclide decays into another nuclide, forming a decay chain, represented as:

$$N_1 \xrightarrow{\lambda_1} N_2 \xrightarrow{\lambda_2} N_3$$

→ **Equilibrium States:**

→→ **Secular Equilibrium:**  $T_1 \gg T_2$ ,

$$A_2 = A_1(1 - e^{-\lambda_2 t}) + A_{20}e^{-\lambda_2 t}$$

→→ **Transient Equilibrium:**  $T_1 \geq T_2$ ,

$$N_2 = \frac{\lambda_1 N_{10}}{\lambda_2 - \lambda_1} (e^{-\lambda_1 t} - e^{-\lambda_2 t}), A_2 = \frac{\lambda_2 A_1}{\lambda_2 - \lambda_1}$$

→→ **No Equilibrium:**  $T_1 < T_2$ ,

$$N_2 = \frac{\lambda_1 N_{10}}{\lambda_1 - \lambda_2} (e^{-\lambda_2 t} - e^{-\lambda_1 t})$$

## G. Counting Statistics and Error Analysis

### G.1. General Aspects on Radiation Measurement and Data

→ **Fundamental Data:** The core data in radiation measurement are counts, which serve as indicators of radiation events.

→ **Types of Errors:**

- **Systematic Errors (Bias):** These impact accuracy due to fixed biases, e.g., calibration errors.
- **Random Errors (Precision):** Variability arising from factors like electronic noise, minimized by large samples.

→ **Accuracy vs Precision:** Accuracy reflects closeness to the true value, while precision indicates measurement repeatability.

### G.2. Statistical Methodology

→ **Descriptive Statistics:** Central tendency measures (mean, median, mode) and variability (variance, standard deviation).

→ **Inferential Statistics:** Used to draw conclusions about population parameters, employing sample data.

### G.3. Statistical Models for Counting Statistics

→ **Binomial Distribution:** Suitable for processes with two outcomes, defined by the probability of success  $p$  and number of trials  $n$ .

→ **Poisson Distribution:** Used when the event probability is low and trials are numerous, approximates binomial for rare events, e.g., radiation counting.

→ **Gaussian (Normal) Distribution:** Approximates distribution with a large sample size or high event mean.

### G.4. Error Estimation and Propagation

→ **Single Measurement Error:** Variance for a Poisson-distributed process is  $\sigma^2 = \mu$ .

→ **Multiple Measurements:**

$$SE = \frac{\sigma}{\sqrt{N}}$$

→ **Error Propagation Formula:**

$$\sigma_u = \sqrt{\left( \frac{\partial u}{\partial x} \sigma_x \right)^2 + \left( \frac{\partial u}{\partial y} \sigma_y \right)^2 + \dots}$$

→ **Chi-Square Test:** Used to test the "goodness of fit" of observed data to expected distributions.

### G.5. Applications of Counting Statistics

→ **Limits of Detectability:**

→→ **ROC Curves:** Analyzes binary decision accuracy using true positive/negative rates.

→→ **Minimum Detectable Amount (MDA):** Defines the smallest reliably detectable signal.

→ **Pulse Time Interval Statistics:** Examines the intervals between pulses to interpret random decay event distributions.

	Time intervals	Counts
Distribution Function	Erlang: $I_n(t) = \frac{(rt)^{n-1} e^{-rt}}{(n-1)!}$	Poisson: $P(n; rt) = \frac{(rt)^n e^{-rt}}{n!}$
Type	Continuous	Discrete
Variable	Time (t)	Count number (n)
Mean	$\tau_n = \frac{n}{r}$	$\bar{n} = rt$
Variance	$\sigma_n^2 = \frac{n}{r^2} = \frac{n}{r}$	$\sigma_p^2 = \bar{n} = rt$

## H. General Properties of detector

### H.1. Detector working mode

→ **Pulse Mode**

→→ **Case 1: Small RC Time Constant ( $t \ll \tau_c$ )**

$$V(t) = R \times i(t)$$

Here,  $i(t)$  represents the instantaneous current at time  $t$ , and  $R$  is the resistance. This is the fast response case, capturing rapid changes in current.

→→ **Case 2: Large RC Time Constant ( $t \gg \tau_c$ )**

$$V_{\text{max}} = \frac{Q}{C}$$

where  $Q$  is the charge collected during the pulse and  $C$  is the capacitance. In this case, the circuit integrates the current over time.

→ **Current Mode**

The total current can be expressed as:

$$I(t) = I_0 \pm \sigma_I(t), \quad I_0 = rQ = r \frac{E}{wq_e}$$

The mean squared value of the current fluctuations is given by:

$$\overline{\sigma_I^2(t)} = \frac{1}{T} \int_{-T}^T [I(t') - I_0]^2 dt' = \frac{1}{T} \int_{-T}^T \sigma_I^2(t') dt'$$

where  $T$  is the measurement time interval. This equation represents the time-averaged variance in current fluctuations.

From Poisson statistics, the standard deviation in the number of events  $n$  over time  $T$  is:

$$\sigma_n = \sqrt{n} = \sqrt{rT}$$

where  $n = rT$  is the mean number of events in the time interval  $T$ . Thus, the fractional standard deviation in current is:

$$\frac{\sigma_I(t)}{I_0} = \frac{\sigma_n}{n} = \frac{1}{\sqrt{rT}}$$

→ **Mean Square Voltage (MSV) Mode**

$$\overline{\sigma_I^2(t)} = \frac{I_0^2}{rT} = \frac{(rQ)^2}{rT} = \frac{rQ^2}{T}$$

**H.2. Key concepts on detector properties**

→ **Pulse height spectra**

→→ Differential PHS:

$$N = \int_{H_1}^{H_2} \frac{dN}{dH} dH$$

→→ Integral PHS:

$$N(H*) = \int_{H*}^{\infty} \frac{dN}{dH} dH$$

→ **Energy resolution:**

$$\text{FWHM} = 2.35\sigma, R = \frac{\text{FWHM}}{N} = \frac{2.35}{\sqrt{N}}$$

→ **The Fano factor,  $F$**

$$F \equiv \frac{\text{observed variance in } N}{\text{Poisson predicted variance}(=N)}$$

Statistical resolution:

$$R|_{\text{statistical limit}} = 2.35\sqrt{\frac{F}{N}}$$

→ **Detector efficiency:**

$$N_{\text{Obs}} = N_{\text{Abs}} \cdot \epsilon_{\text{tot}} = N_{\text{Abs}} \cdot W(\Theta, \Phi) \cdot \epsilon_{\text{geo}} \cdot \epsilon_{\text{intrinsic}} \cdot \epsilon_{\text{electronic}}$$

→ **Dead time Assume:**  $n$  = true event rate,  $m$  = measured events rate,  $T$  = average period between true events ( $=1/n$ ),  $\tau$  = system dead time

→→ **Nonparalyzable Model:** fixed dead time

$$m = \frac{n}{1 + n\tau}, n = \frac{m}{1 - m\tau}$$

→→ **Paralyzable Model:** extendable dead time

$$m = ne^{-n\tau}, n = -\frac{W(-m\tau)}{\tau}$$

Dead Time Measurement: two source method

$$n_{12} + n_b = n_1 + n_2$$

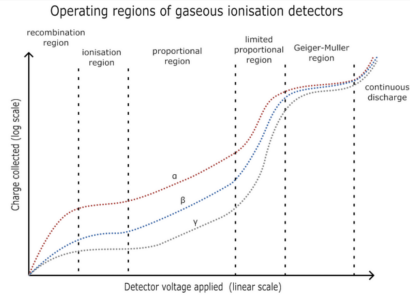
→→ **Nonparalyzable Model:**

$$\tau = \frac{m_1 m_2 - \sqrt{m_1 m_2 (m_{12} - m_1)(m_{12} - m_2)}}{m_1 m_2 m_{12}}$$

→→ **Paralyzable Model:**

$$\tau = \frac{2m_{12}}{(m_1 + m_2)^2} \ln \left( \frac{m_1 + m_2}{m_{12}} \right)$$

**I. Gas-filled Detector**



- Ionization region: ionization chambers
- Proportional region: proportional counters
- Geiger-Mueller region: Geiger counters

**I.1. Ionization Chambers**

→ Average number of ion pairs:

$$\langle n_T \rangle = \frac{L \cdot \left\langle \frac{dE}{dx} \right\rangle_i}{W_i}$$

→ The drift velocity of charge in a gas

$$v = \mu \frac{\mathcal{E}}{p}$$

- - No internal gain (gain  $\sim 1$ ).
- Slow drift velocity ( $v_e \sim 10^3 \text{ m/s}$ ,  $v_{ion} \sim 1 \text{ m/s}$ ).
- Charge collection time is too slow to count individual pulses.
- Poor timing properties.
- Exposure: defined as the amount of ionization charge per unit mass of air

$$X \equiv \frac{Q}{M}$$

Convert exposure to dose  $D = X \times 33.7 [\text{Gy}]$

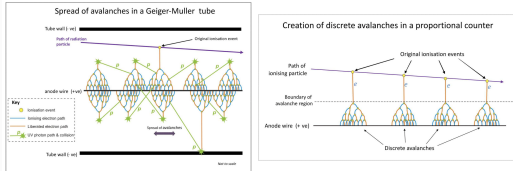
**I.2. Proportional Counters**

→

$$\mathcal{E} = \frac{V}{r \ln(b/a)}$$

$a$  = anode wire radius,  $b$  = cathode inner radius.

→ nobel gas (such as Ar) + “quench gas” (such as CH4)



**I.3. Geiger-Mueller Tubes(G-M counters)**

→ Chain avalanche leads to Geiger discharge

- Primary Geiger discharge
- Secondary Geiger discharge(UV photons)

→ A cloud of positive ions surrounds the anode, with the effect of reducing the electric field intensity, leads the Geiger discharge termination – called Quenching effect.

Detector Type	Avalanche amplification	Good timing?	Energy information	Use as monitor
Ion chamber	none	no, $\sim 10^{-2}$ s	none	yes
Prop. counter	$10^3 - 10^5$	yes, $\sim 10^{-6}$ s	yes	no
G-M tube	$\sim 10^{10}$	yes, $\sim 10^{-6}$ s	none	yes

**J. Semi-conductor Detector**

**J.1. Advantages of semiconductor detectors**

- Semiconductor with moderate bandgap (1-2 eV)
- Thermal energy =  $1/40 \text{ eV}$
- Energy to create e/h pair (signal quanta) w  $3.6 \text{ eV}$  ( c.f gas:  $w = 35 \text{ eV}$ )
- High charge carrier yield
- Better energy resolution and large signal
- High density and Z (comparing to gas)
- High carrier mobility: Fast ( $< 30 \text{ ns}$ )

**J.2. Basic properties of semiconductor**

Majority of charge carriers provided by donors (impurities; doping)

- n-type:majority carriers are electrons(pentavalent dopants)

- p-type:majority carriers are positive holes(trivalent dopants)

• Pentavalent dopants (electron donors): P, As, Sb, ...

• 5th electron only weakly bound; easily excited into conduction band]

• Trivalent dopants (electron acceptors): Al, B, Ga, In, ...

[One unsaturated binding; easily accepts valence electron leaving hole]

→ PN Junction: depletion depth

$$d \approx \sqrt{\frac{2\epsilon V}{eN}} = \sqrt{2\epsilon V \mu p}, \quad V_{\text{bias}} = \frac{eNd^2}{2\epsilon}, \quad \rho = \frac{1}{e(\mu_n n + \mu_p p)}$$

$$C = \frac{\epsilon A}{d} = A \sqrt{\frac{e\epsilon N}{2V}}$$

→ Noise sources: ( ENC= Equivalent Noise Charge)

Capacitance:  $\text{ENC} \propto C_d$

Leakage Current:  $\text{ENC} \propto \sqrt{I}$

Thermal Noise:  $\text{ENC} \propto \sqrt{k_B T / R}$

**J.3. Photodiode (PD)**

→ Cut-off wavelength vs Energy bandgap

$$\lambda_g [\mu\text{m}] = \frac{1.24}{E_{\text{gap}} [\text{eV}]}$$

→ Photon attenuation

$$I(x) = I_0 e^{-\alpha x}$$

→ Photocurrent and responsivity

$$I_{ph} = q \left( \frac{P_0}{h\nu} \right) (1-r)(1-e^{-\alpha d}), \quad R = \frac{I_{ph}}{P_0} = \frac{q}{h\nu} (1-r)(1-e^{-\alpha d})$$

→ Quantum Efficiency(external and internal)

$$\eta_e = \frac{I_{ph}/q}{P_0/h\nu} = (1-r)[1 - e^{-\alpha d}], \eta_i = \frac{\eta_e}{(1-r)} = 1 - e^{-\alpha d} \cong 1$$

→ Avalanche Photodiodes: current gain and responsivity

$$M = \frac{\text{Multiplied photocurrent}}{\text{Primary photocurrent}} = \frac{I_M}{I_p}, R_{\text{APD}} = \frac{\eta q}{h\nu} M = R_0 M$$

→ Response Time: transit time, diffuse time and RC time constant

$$t_d = \frac{W}{v_D}, t_{\text{diff}} = \frac{l^2}{2D_e}, \tau = \tau_T C_T$$

Type	PMT	APD	SiPM
Amplification	High ( $10^6$ )	Low ( $\sim 10^2$ )	High ( $10^6$ )
Magnetic field	Sensitive	Not sensitive	Not sensitive
Compactness	bulky	compact	compact
Bias (V)	HV (600-1200)	HV (300-1500)	20-70
S/N ratio	High	Low	High
Time resolution	$\sim 1 \text{ ns}$	$> 1 \text{ ns}$ (2-4 ns)	$< 1 \text{ ns}$ ( $\sim 200\text{ps}$ )
Electronic readout	Voltage amplifier	Charge sensitive preamplifier	Voltage amplifier

**K. Scintillation Detector**

**K.1. General characteristics of scintillation detector**

- High stopping power, density and Z

- Sensitivity to radiation energy
  - Scintillation efficiency and light yield
  - Fast time response
  - Pulse shape discrimination
  - Radiation hardening
  - Usually expensive
- **Stokes Shift:** emitted photons are at longer wavelengths (smaller energies) than the energy gap of the excitation. This allows the scintillation light to propagate through the material. Emitted photons can't be self-absorbed by exciting the material again
- **Light Output and Light Yield**

$$L = L_0 \left( e^{-t/\tau_d} - e^{-t/\tau_r} \right), Y = \int_0^\infty L(t) dt$$

→ **Scintillation Efficiency**

$$\eta = \frac{Y \cdot \frac{hc}{\lambda}}{E}$$

**K.2. Scintillators**

→ **Inorganic Scintillators:** Intrinsic(self-activated)/Extrinsic(activated)

→ Efficiency for conversion of energy deposit to scintillation light

$$\eta = \beta SQ$$

where  $\beta$ – efficiency of energy conversion,  $S$  – efficiency of energy transfer,  $Q$  – quantum efficiency of luminiscent centers

→ **Three mechanisms for scintillation**

- Excitons (bound e-h pair)

- Defects (interstitial)

- activators (doped impurities): trace mounts of activators are purposely introduced to create some narrower levels within the forbidden band gap. E.g. NaI(Tl), CsI(Tl)

→ **Organic Scintillators:**low density; just C and H; photoelectric effect goes as  $Z^4$

→ **Molecular states:** • Singlet states (spin=0)

- A series of levels (vibration states) – Gap between  $S_0$  and  $S_1$  is 3-4 eV

• Triplet states (spin=1)

Two scintillation processes:

Fluorescence :  $S_1 \rightarrow S_0$  [ns] / Phosphorescence:  $T_0 \rightarrow S_0$  [ms]

→ Light yield and Birk's law:

$$\frac{dL}{dx} = S \frac{dE}{dx}, \frac{dL}{dx} = \frac{S \frac{dE}{dx}}{1 + k_B \frac{dE}{dx}}$$

**K.3. Photomultiplier Tube (PMT)**

→ **Gain:**

$$G = \delta^N = 10^6 - 10^8, \frac{dG}{G} = N \frac{dV_d}{V_d} = N \frac{dV_a}{V_a}$$

→ **Causes of dark current include:**

- Thermionic emission from photocathode and dynodes

- Leakage current between anode and other electrodes

- Photocurrent by scintillation from glass or electrode supports

- Field emission current

- Cosmic rays, radioactivity in glass envelope, radioactivity (gamma) from surroundings (cement)

→ **Energy Resolution:**  $N_e = x\delta\delta, \sigma_F^2(N_e) = \sigma_F^2(x) + \sigma_F^2(xp) + \sigma_F^2(xp\delta)$

$$\sigma_F^2(N_e) = \frac{1}{x} + \frac{1}{x} \frac{1-p}{p} + \frac{1}{xp} \frac{1}{(\delta-1)}$$

$$R_E = 2.35 \sqrt{\frac{1}{x} \left( 1 + \frac{1-p}{p} + \frac{1}{p(\delta-1)} \right)}$$

Type	Mechanism		Device	Energy Proportionality	Counting rate Performance	Temporal Information	Position Information
	Interaction	Signal					
Gas-filled	Ionization charges	Collect ions	Ion Chamber	Excellent	Low $\downarrow$	Poor	Average
		Multiply & Collect ions	Prop. Chamber	Very good	$\downarrow$	Average	Good
		Create discharge	GM Counter & Spark chamber	No	$\downarrow$	Good to Excellent	Excellent*
Semi-conductor	Ionization charges	Collect ions	Silicon Diode & CDT	Excellent	$\downarrow$	Average	Excellent
Scintillator	Excitation light	Convert light into electrons	Scintillation Detector	Acceptable	$\downarrow$	Excellent	Poor*
Gas-filled Current	Ionization charges	Collect current	Ion Chamber	Radiation Field	High $\downarrow$	None	None